

ABSTRACT

A semiconductor storage device of an embodiment includes a substrate, a plurality of first conductive layers, pillar, and a second conductive layer. The plurality of first
5 conductive layers are provided above the substrate, and mutually separated in a first direction. The pillar is provided to penetrate the plurality of the first conductive layers, and includes a first semiconductor layer extending in the first direction. A part of the pillar that intersects
10 with the first conductive layers are functioned as memory cells. The second conductive layer is provided above the plurality of first conductive layers and is in contact with the first semiconductor layer. The second conductive layer is made of a metal or a silicide.